1N5550/US 1N5551/US 1N5552/US 1N5553/US 1N5554/US

TECHNICAL DATA DATA SHEET 126, REV E

SEMICONDUCTOR

SENSITRON



HIGH CURRENT AXIAL LEAD RECTIFIERS

DESCRIPTION: 200-1000 VOLT, 3.0 AMP, 2000 NANOSECOND RECTIFIER

-Suffix "US" denotes melf/surface mount packaging

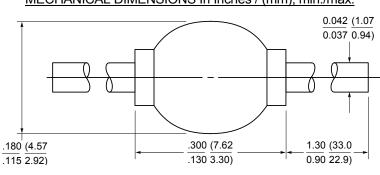
MAX. RATINGS / ELECTRICAL CHARACTERISTICS All ratings are at $T_A = 25^{\circ}C$ unless otherwise specified.

RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV) 1N5550 1N5551 1N5552 1N5553 1N5554	_	-	-	200 400 600 800 1000	Vdc
Average DC Output Current (I₀)	T _A = +55 °C	-	-	3.0	Amps
Peak Single Cycle Surge Current (I _{fsm})	t _p = 8.3 ms Single Half Cycle Sine Wave, Superimposed On Rated Load	-	-	150	Amps(pk)
Operating and Storage Temp. (T _{op} & T _{sta})	-	-65	-	+175	°C
Maximum Forward Voltage (V _f) 1N5550 1N5551 1N5552 1N5553 1N5554	I _f = 9.0A (300 μsec pulse, duty cycle < 2%)	-	-	1.2 1.2 1.2 1.3 1.3	Volts
Maximum Instantaneous Reverse Current At Rated (PIV)	T _A = 25° C T _A = 100° C	-	-	1.0 75	μAmps
Reverse Recovery Time (t_{rr})	I _f = 0.5A, I _r = 1.0A, I _{rr} = 0.25A	-	-	2000	nsec
Thermal Resistance (θ_{JL})	Junction to Lead d = 0.375"			22	°C/W
Thermal Resistance (θ_{JEC})	Junction to Endcap	-	-	11	° C/W



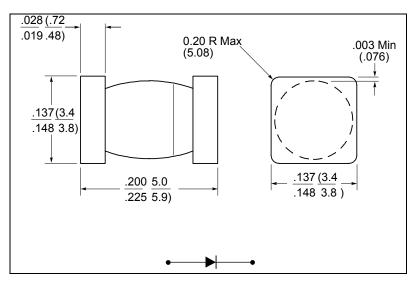


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MECHANICAL DIMENSIONS In Inches / (mm), min./max.

PKG. 301



Note: The cathode side is marked with a dark colored band on one side of the diode body.

MELF-B

Note: The cathode side is marked on body with a dark band.



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